



Description

The NVMFS4C03NWFET1G uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 150A$

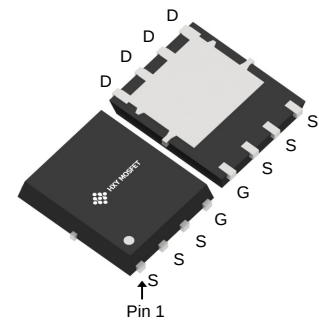
$R_{DS(ON)} < 2.4m\Omega$ $V_{GS}=10V$

Application

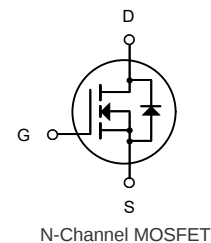
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NVMFS4C03NWFET1G	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	150	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	106	A
I_{DM}	Pulsed Drain Current	450	A
EAS	Single Pulse Avalanche Energy	625	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	150	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	1.6	$^\circ C/W$



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =17A	---	1.5	2	mΩ
		V _{GS} =4.5V, I _D =17A	---	2.3	3	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1	---	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =30V, V _{GS} =0V, T _J =100°C	---	---	100	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =17A	---	46	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	0.88	---	Ω
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _D =17A	---	105	---	nC
Q _{gs}	Gate-Source Charge		---	20	---	
Q _{gd}	Gate-Drain Charge		---	20	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω	---	13	---	ns
T _r	Rise Time		---	30	---	
T _{d(off)}	Turn-Off Delay Time		---	85	---	
T _f	Fall Time		---	50	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	6040	---	pF
C _{oss}	Output Capacitance		---	627	---	
C _{rss}	Reverse Transfer Capacitance		---	551	---	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	150	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =17A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=17A, di/dt=100A/μs, T _J =25°C	---	28	---	nS
Q _{rr}	Reverse Recovery Charge		---	16	---	nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.

Notes 2.EAS condition: T_J=25°C, V_{DD}=30V, V_G=10V, R_g=25Ω, L=0.5mH.

Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Characteristics

Figure 1. Output Characteristics

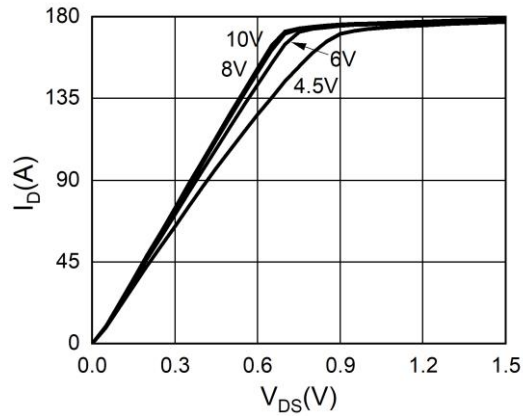


Figure 2. Transfer Characteristics

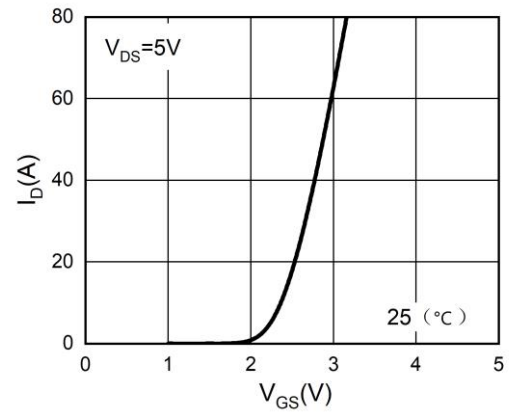


Figure 3. Power Dissipation

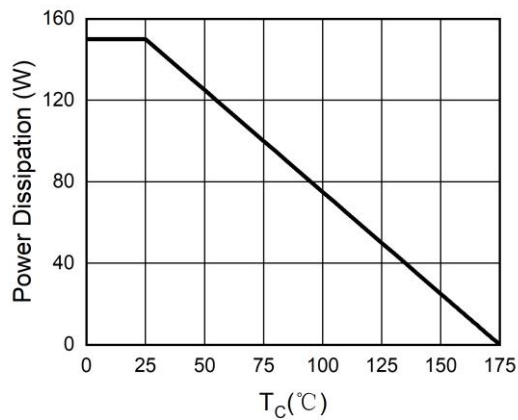


Figure 4. Drain Current

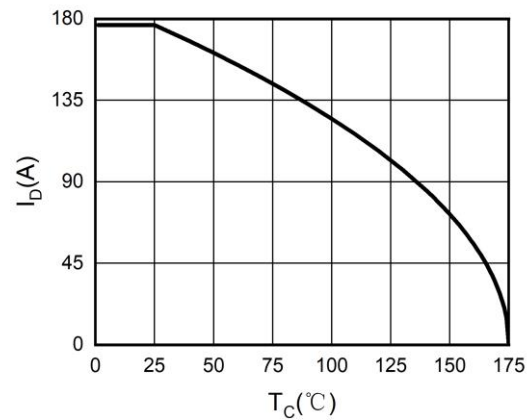


Figure 5. BV_{DSS} vs Junction Temperature

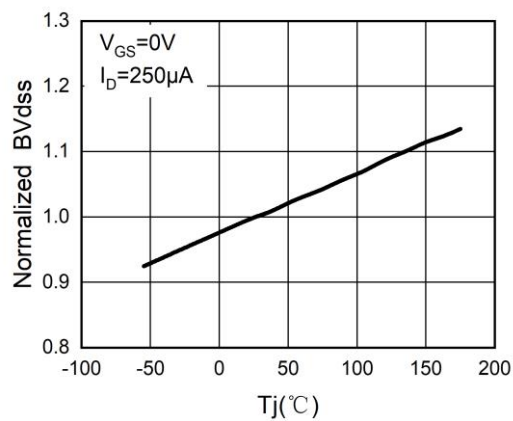


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

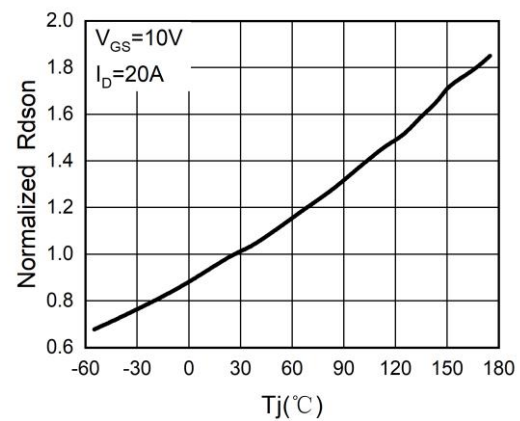




Figure 7. Gate Charge Waveforms

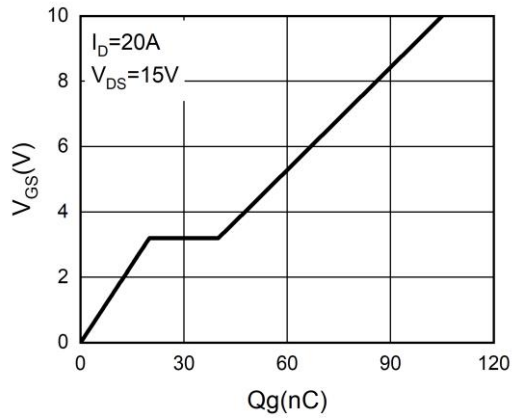


Figure 8. Capacitance

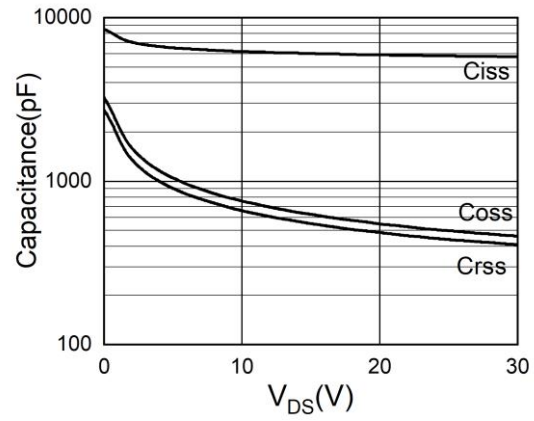


Figure 9. Body-Diode Characteristics

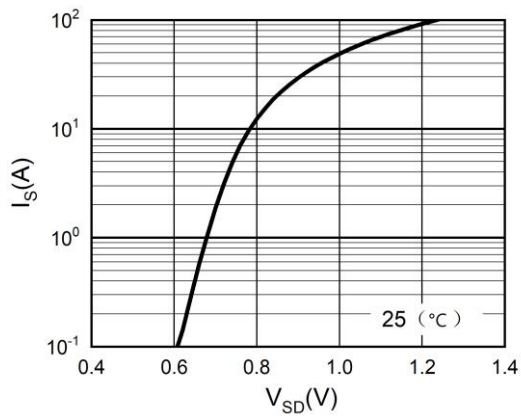
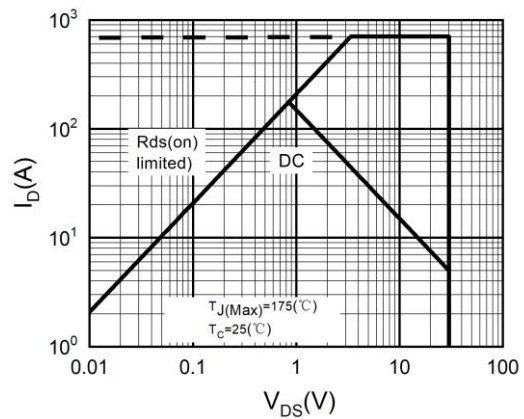


Figure 10. Maximum Safe Operating Area





Test Circuit

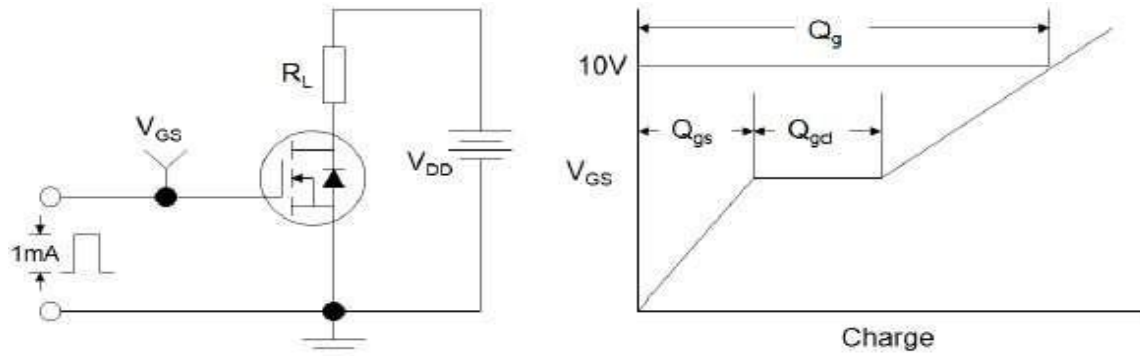


Figure1:Gate Charge Test Circuit & Waveform

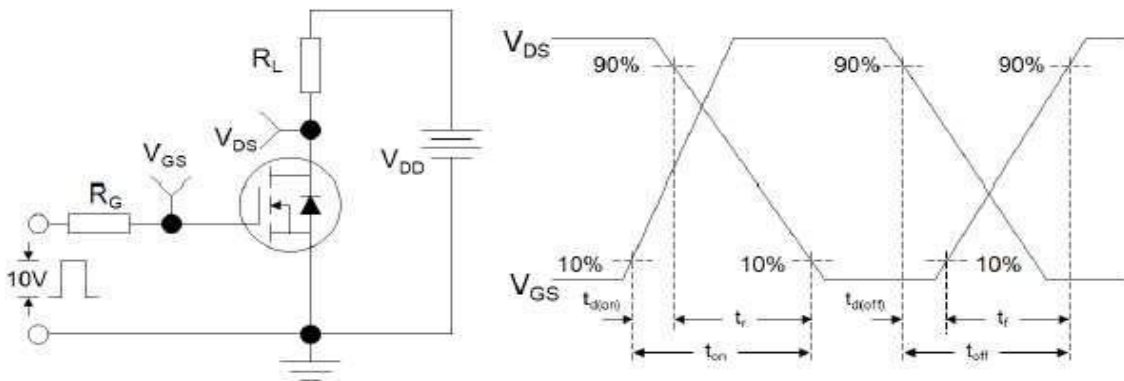


Figure 2: Resistive Switching Test Circuit & Waveforms

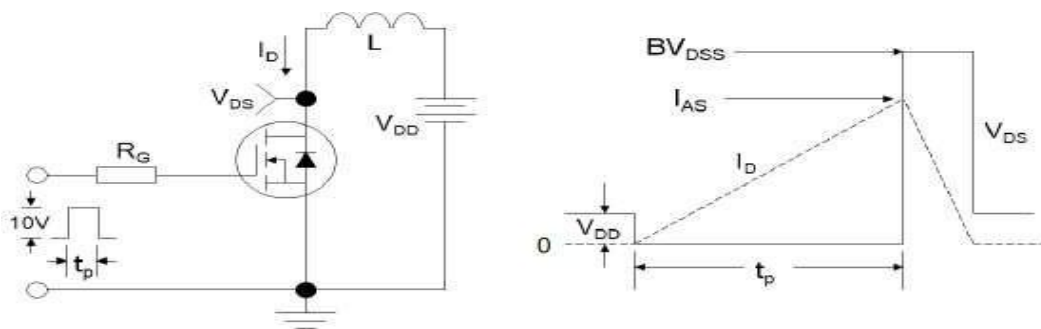
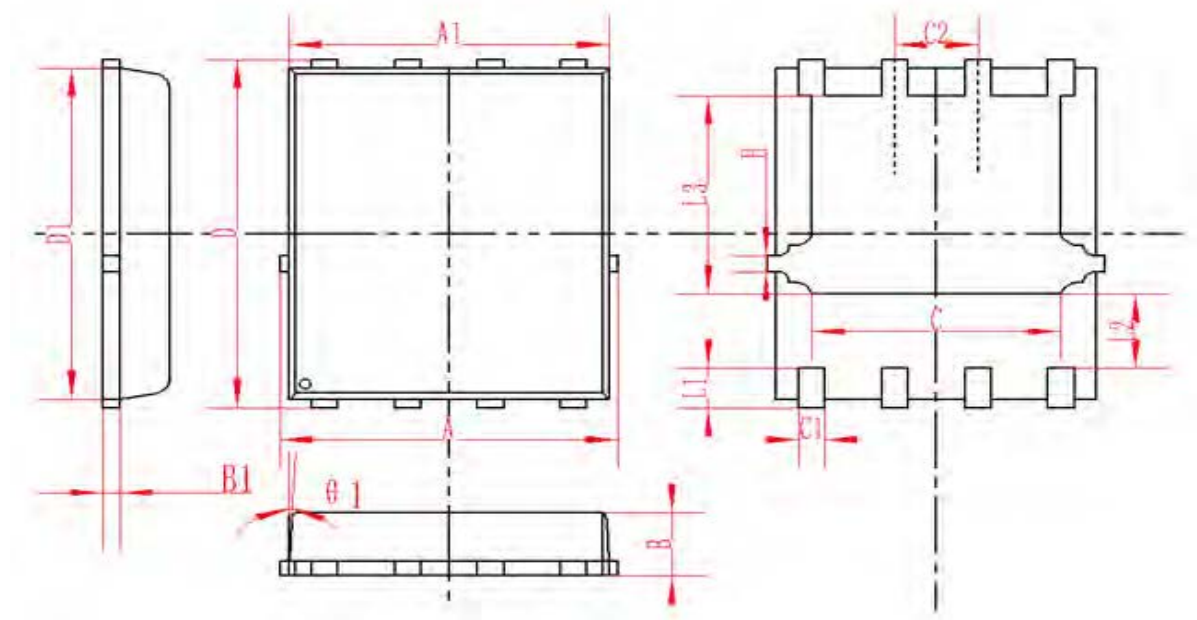


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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